

FDT439N

N-Channel 2.5V Specified Enhancement Mode Field Effect Transistor

General Description

This N-Channel Enhancement mode field effect transistor is produced using Fairchild Semiconductor's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize onstate resistance, and provide superior switching performance. These products are well suited to low voltage, low current applications such as notebook computer power management, battery powered circuits, and DC motor control.

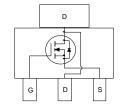
Features

- 6.3 A, 30 V. $R_{DS(on)} = 0.045 \ \Omega \ @V_{GS} = 4.5 \ V$ $R_{DS(on)} = 0.058 \ \Omega \ @V_{GS} = 2.5 \ V$
- Fast switching speed.
- High power and current handling capabitlity in a widely used surface mount package.

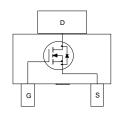
Applications

- DC/DC converter
- Load switch
- Motor driving









Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	FDT439N	Units	
V_{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		<u>+</u> 8	V
I _D	Drain Current - Continuous	(Note 1a)	6.3	А
	- Pulsed		20	
P _D	Power Dissipation for Single Operation	(Note 1a)	3	W
		(Note 1b)	1.3	
		(Note 1c)	1.1	
T _J , T _{stg}	Operating and Storage Junction Temperature	-55 to +150	∘C	

Thermal Characteristics

$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	42	∘C/W
$R_{\theta^{JC}}$	Thermal Resistance, Junction-to-Case	(Note 1)	12	∘C/W

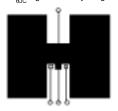
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDT439N	FDT439N	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics				I.	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		40		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -8 V, V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.4	0.67	1	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to $25^{\circ}C$		-2.2		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 6.3 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 6.3 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 2.5 \text{ V}, I_D = 5.5 \text{A}$		0.038 0.055 0.048	0.045 0.072 0.058	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = 4.5 V, V _{DS} = 5 V	10			Α
g FS	Forward Transconductance	V _{DS} = 5 V, I _D = 6.3 A		17		S
Dvnamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		500		pF
Coss	Output Capacitance	f = 1.0 MHz		185		pF
C _{rss}	Reverse Transfer Capacitance			43		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A},$		6	12	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		10	18	ns
t _{d(off)}	Turn-Off Delay Time			30	48	ns
t _f	Turn-Off Fall Time			10	18	ns
Qg	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_D = 6.3 \text{ A},$		10.7	15	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 4.5 V$,		0.9		nC
Q _{gd}	Gate-Drain Charge			3.7		nC
Drain-Sc	ource Diode Characteristics and	d Maximum Ratings				
Is	Maximum Continuous Drain-Source Did				2.5	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2.5 \text{ A}$ (Note 2)		0.8	1.2	V

Notes:

^{1.} $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 42° C/W when mounted on a 1 in² pad of 2 oz. copper.



b) 95° C/W when mounted on a 0.066 in² pad of 2 oz. copper.



c) 110° C/W when mounted on a minimum mounting pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics

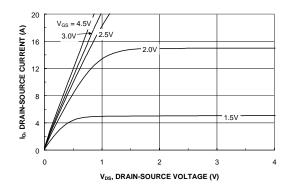


Figure 1. On-Region Characteristics.

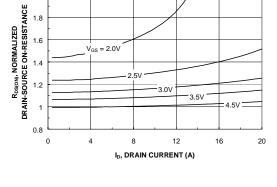


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

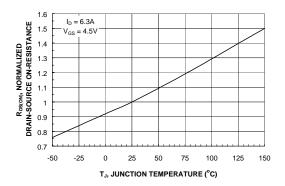


Figure 3. On-Resistance Variation with Temperature.

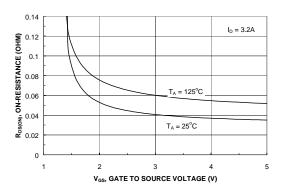


Figure 4. On-Resistance Variation with Gate-To-Source Voltage.

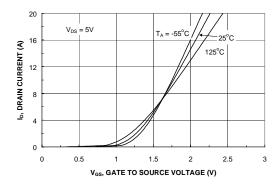


Figure 5. Transfer Characteristics.

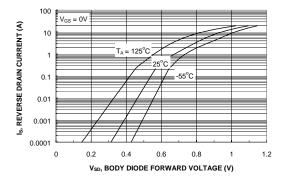
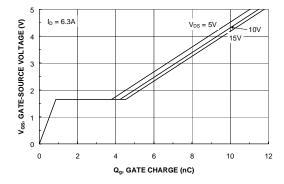


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



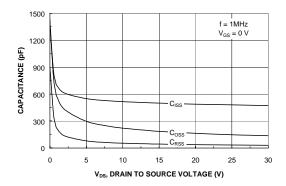
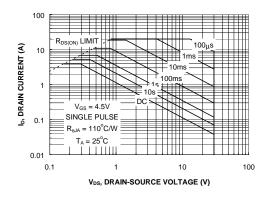


Figure 7. Gate-Charge Characteristics.

Figure 8. Capacitance Characteristics.



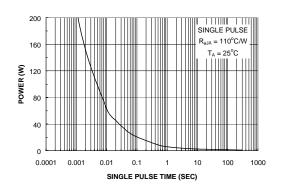


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

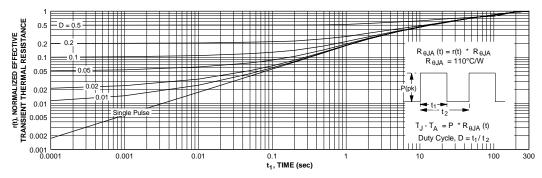
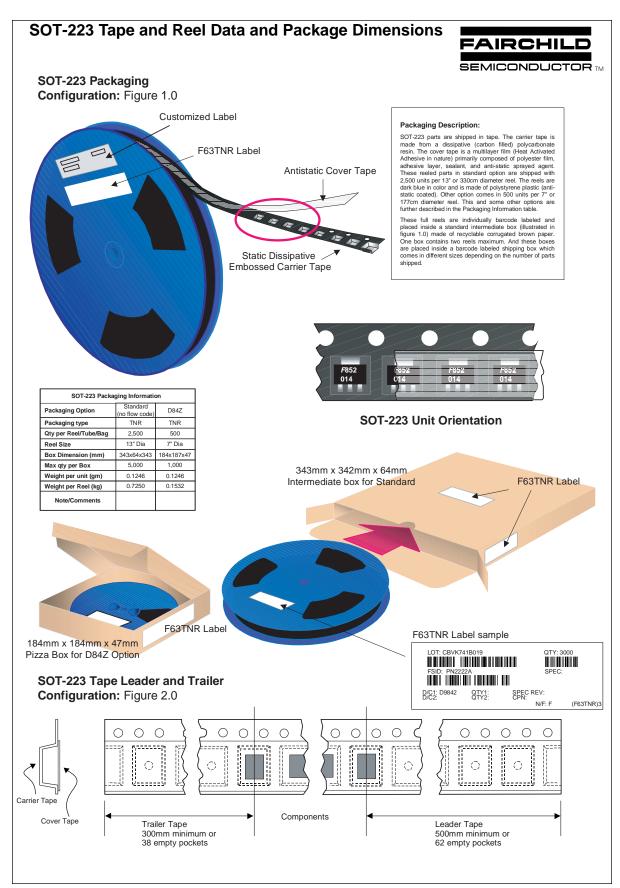


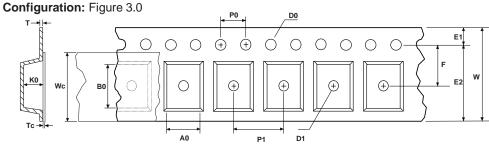
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient themal response will change depending on the circuit board design.





SOT-223 Embossed Carrier Tape



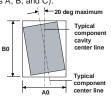
User Direction of Feed	
	$\overline{}$

	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-223 (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



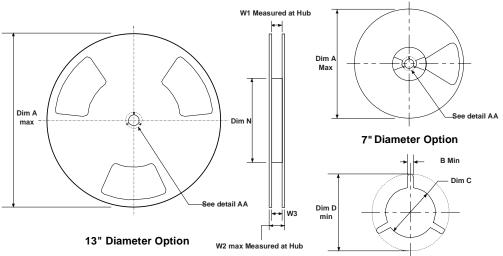
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

DETAIL AA

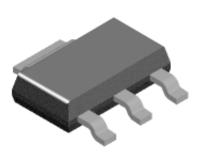
SOT-223 Reel Configuration: Figure 4.0

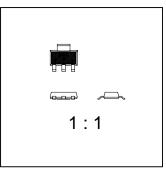


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SOT-223 Tape and Reel Data and Package Dimensions, continued

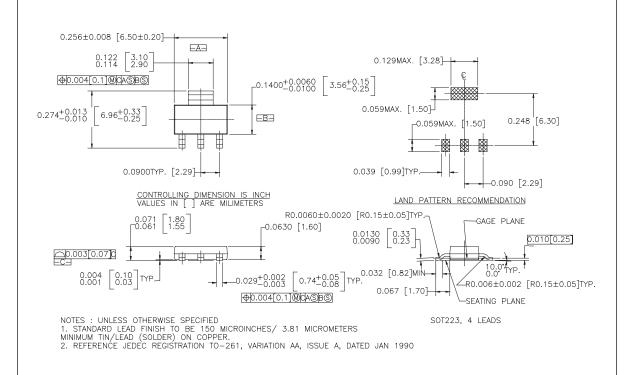
SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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